

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- Trench MOSFET technology
- AEC-Q101 qualified

### 3. Applications

- DC to DC conversion
- High-speed line driver
- High-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C	-	-	-20	V
V <sub>GS</sub>	gate-source voltage		-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>sp</sub> = 25 °C	-	-	-18	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C	-	-	19	W
Static chara	octeristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -6 A; T <sub>j</sub> = 25 °C	-	30	38	mΩ



# 5. Pinning information

Table 2	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	D	drain		D					
2	D	drain							
3	G	gate	2						
4	S	source	3 8 4						
5	D	drain	Transparent top view						
6	D	drain	DFN2020MD-6 (SOT1220)	s					
7	D	drain		017aaa259					
8	S	source							

# 6. Ordering information

#### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK4D38-20P		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK4D38-20P	6F

20 V, P-channel Trench MOSFET

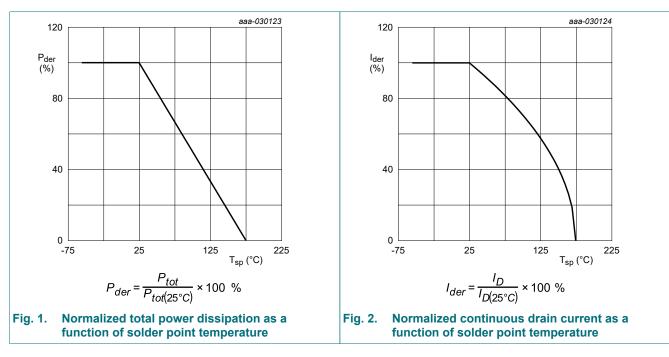
## 8. Limiting values

#### Table 5. Limiting values

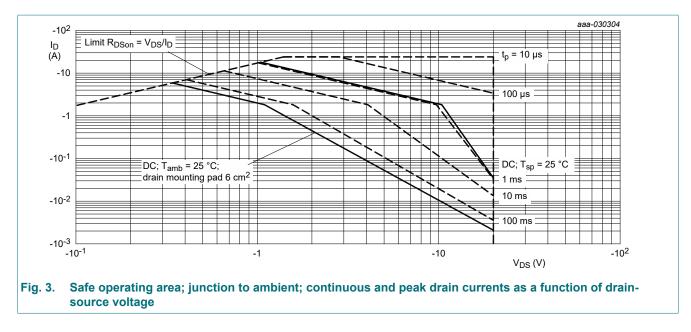
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage	_		-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>sp</sub> = 25 °C		-	-18	А
		V <sub>GS</sub> = -4.5 V; T <sub>sp</sub> = 100 °C		-	-11	А
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-6	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-72	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	19	W
		T <sub>amb</sub> = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C		-	-19	А
		T <sub>amb</sub> = 25 °C	[1]	-	-2	А
I <sub>SM</sub>	peak source current	single pulse; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	-75	А
ESD maximu	um rating		·			
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche r	uggedness		·			
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.5 A; DUT in v avalanche (unclamped)		-	15	mJ
	I					

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
 Measured between all pins.



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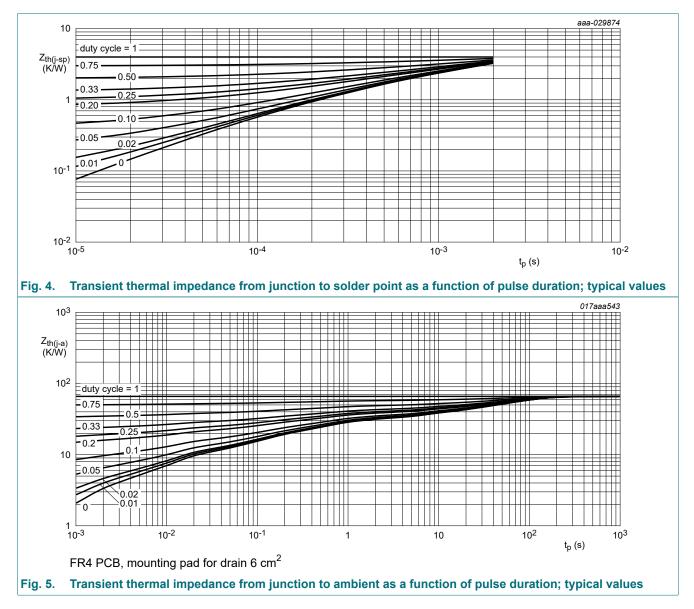


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## 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	4	8	K/W

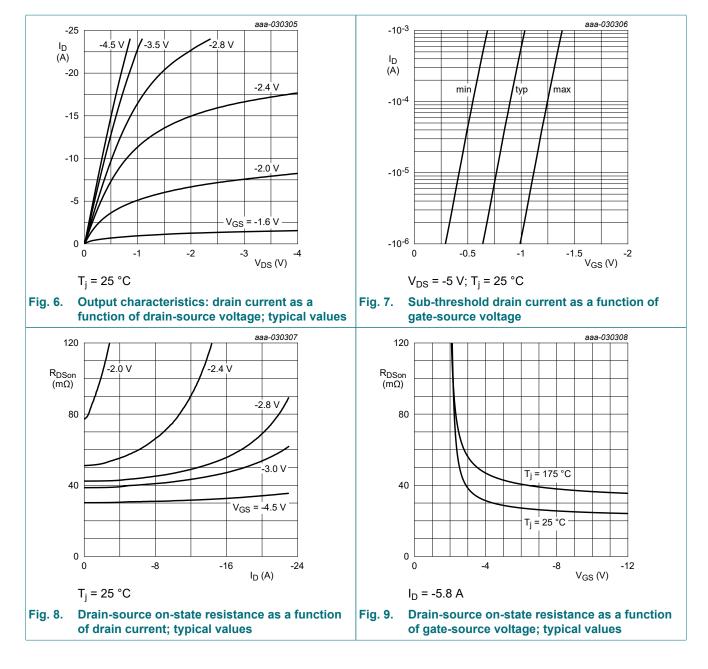
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



## **10. Characteristics**

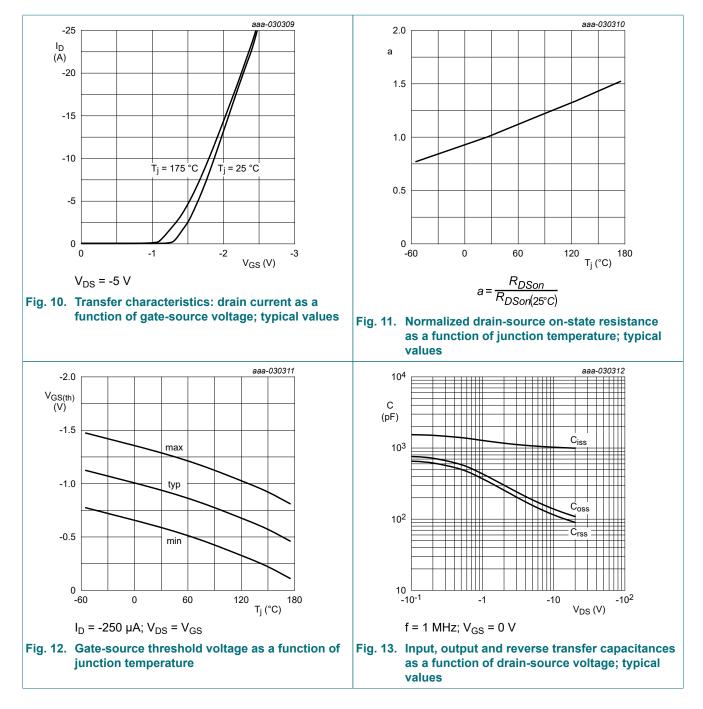
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = -250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.6	-0.95	-1.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	-20	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-2	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -8 V; I <sub>D</sub> = -6 A; T <sub>j</sub> = 25 °C	-	26	33	mΩ
		V <sub>GS</sub> = -8 V; I <sub>D</sub> = -6 A; T <sub>j</sub> = 175 °C	-	40	50	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -6 A; T <sub>j</sub> = 25 °C	-	30	38	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 25 °C	-	46	64	mΩ
9fs	forward transconductance	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -6 A; T <sub>j</sub> = 25 °C	-	20	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	21	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -5.8 A; $V_{GS}$ = -4.5 V;	-	10.6	16	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	3.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1025	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	137	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	113	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; I <sub>D</sub> = -5.8 A; V <sub>GS</sub> = -4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	17	-	ns
d(off)	turn-off delay time	-	-	23	-	ns
f	fall time	1	-	19	-	ns
Source-drai	in diode		1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.8	-1.2	V
rr	reverse recovery time	$I_{S} = -2 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	17	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = -10 V; T <sub>j</sub> = 25 °C	_	5	_	nC

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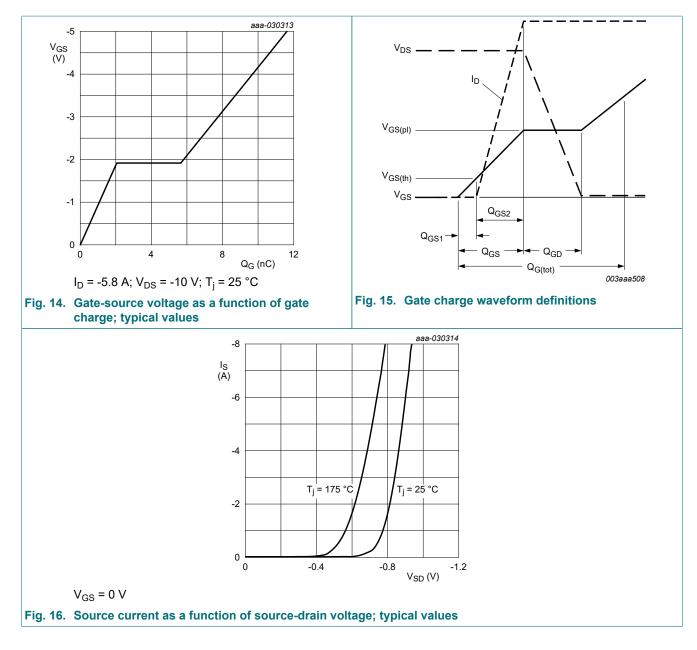


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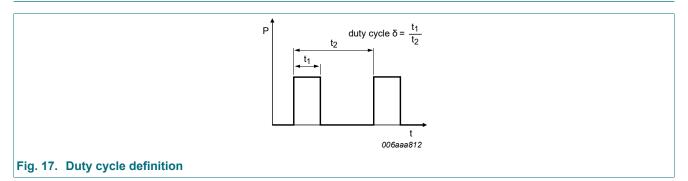
#### 20 V, P-channel Trench MOSFET



#### 20 V, P-channel Trench MOSFET



# **11. Test information**

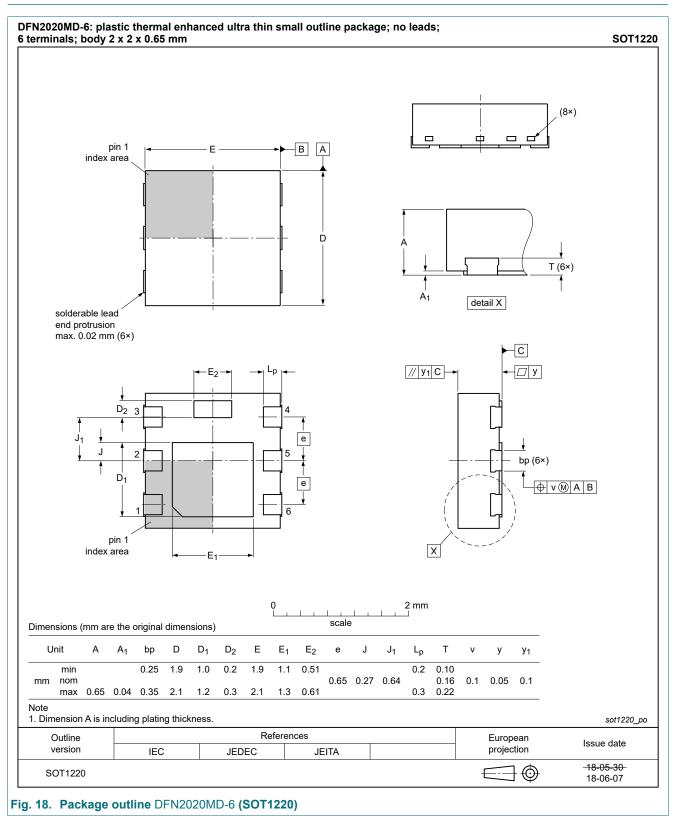


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

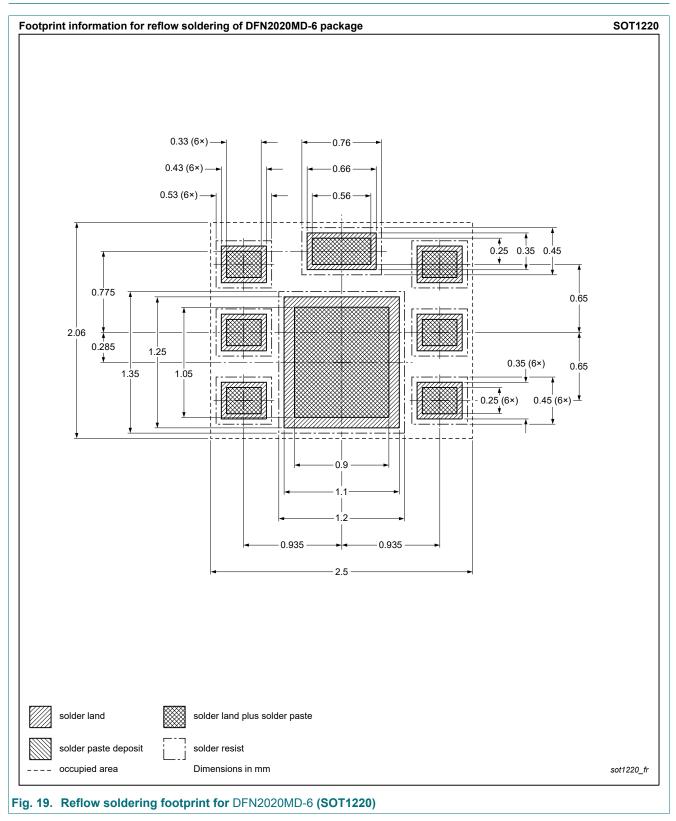
#### 20 V, P-channel Trench MOSFET

## 12. Package outline



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## 13. Soldering



# 14. Revision history

Table 8. Revision history           Data sheet ID         Release date         Data sheet status         Change notice         Supersedes							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D38-20P v.3	20200709	Product data sheet	-	BUK4D38-20P v.2			
Modifications:	Product status	changed.	•				
BUK4D38-20P v.2	20200121	Objective data sheet	-	BUK4D38-20P v.1			
BUK4D38-20P v.1	20191025	Objective data sheet	-	-			

BUK4D38-20P

# 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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